

# **Maximum Ratings** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteris	Symbol	Value	Unit		
Drain-Source Voltage	V <sub>DSS</sub>	30	V		
Gate-Source Voltage			V <sub>GSS</sub>	±20	V
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	Steady State	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	11 8.5	А
	t<10s	$T_A = +25^{\circ}C$ $T_A = +70^{\circ}C$	I <sub>D</sub>	14 11	А
Continuous Drain Current (Note 6) V <sub>GS</sub> = 10V	Steady State	$T_{C} = +25^{\circ}C$ $T_{C} = +100^{\circ}C$	I <sub>D</sub>	30 20	А
Pulsed Drain Current (10µs pulse, duty cycle = 1%)			I <sub>DM</sub>	90	А
Avalanche Current (Note 7) L = 0.1mH			I <sub>AS</sub>	12.7	А
Avalanche Energy (Note 7) L = 0.1mH			E <sub>AS</sub>	8.1	mJ

### **Thermal Characteristics**

Characteristic		Symbol	Value	Units
Total Power Dissipation (Note 5)		$P_D$	0.9	W
Thermal Resistance, Junction to Ambient (Note 5)	Steady State	5	137	°C/W
	t < 10s	R <sub>0JA</sub>	90	°C/W
Total Power Dissipation (Note 6)		$P_D$	2.4	W
Thermal Pegistance Junction to Ambient (Note 6)	Steady State	D	52	°C/W
Thermal Resistance, Junction to Ambient (Note 6)	t < 10s	$R_{\theta JA}$	35	°C/W
Total Power Dissipation (Note 6)	Tc = +25°C	$P_D$	26	W
Thermal Resistance, Junction to Case (Note 6)		$R_{ heta JC}$	4.8	°C/W
Operating and Storage Temperature Range		$T_{J}, T_{STG}$	-55 to +150	°C

## **Electrical Characteristics** (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур	Max	Unit	Test Condition	
OFF CHARACTERISTICS (Note 8)							
Drain-Source Breakdown Voltage	BV <sub>DSS</sub>	30	_	_	V	$V_{GS} = 0V, I_D = 250\mu A$	
Zero Gate Voltage Drain Current T <sub>J</sub> = +25°C		l	_	1	μΑ	V 20V V 0V	
Zero Gate Voltage Drain Current T <sub>J</sub> = +150°C (Note 9)	I <sub>DSS</sub>	l	_	100	μΑ	$V_{DS} = 30V$ , $V_{GS} = 0V$	
Gate-Source Leakage	I <sub>GSS</sub>		_	±100	nA	$V_{GS} = \pm 20V, V_{DS} = 0V$	
ON CHARACTERISTICS (Note 8)							
Gate Threshold Voltage	$V_{GS(th)}$	1.0	_	2.5	V	$V_{DS} = V_{GS}$ , $I_D = 250\mu A$	
Static Drain-Source On-Resistance		_	6.5	8.5	mΩ	$V_{GS} = 10V, I_D = 18A$	
Static Diain-Source On-Nesistance	R <sub>DS(ON)</sub>	1	8	10.5	11122	$V_{GS} = 4.5V, I_D = 16A$	
Diode Forward Voltage	$V_{SD}$		0.75	1.0	V	$V_{GS} = 0V$ , $I_S = 1A$	
On State Drain Current (Note 9)	I <sub>D(ON)</sub>	10	_	_	Α	$V_{DS} \leq 5V$ , $V_{GS} = 4.5V$	
DYNAMIC CHARACTERISTICS (Note 9)							
Input Capacitance	C <sub>iss</sub>	_	2,075	4,150		V <sub>DS</sub> = 15V, V <sub>GS</sub> = 0V, f = 1.0MHz	
Output Capacitance	Coss	1	190	380	pF		
Reverse Transfer Capacitance	C <sub>rss</sub>		138	276		1 – 1.01/11/12	
Gate Resistance	$R_g$	_	2.4	5	Ω	$V_{DS} = 0V, V_{GS} = 0V, f = 1.0MHz$	
Total Gate Charge (V <sub>GS</sub> = 4.5V)	Qg		16.1	32		V <sub>DS</sub> = 15V, I <sub>D</sub> = 18A	
Total Gate Charge (V <sub>GS</sub> = 10V)	$Q_g$	_	37	74	nC		
Gate-Source Charge	Q <sub>gs</sub>		6.1	12	iiC		
Gate-Drain Charge	$Q_{gd}$	_	5.9	12			
Turn-On Delay Time	t <sub>D(on)</sub>		4.5	10		$V_{DS} = 15V, V_{GS} = 10V,$ $R_{L} = 0.83\Omega, R_{GEN} = 3\Omega,$	
Turn-On Rise Time	t <sub>r</sub>		19.6	35	20		
Turn-Off Delay Time	t <sub>D(off)</sub>	_	31	50	ns		
Turn-Off Fall Time	t <sub>f</sub>		10.7	21			
Reverse Recovery Time	t <sub>rr</sub>		13.7	27	ns		
Reverse Recovery Charge	Q <sub>rr</sub>	1	18.3	37	nC	I <sub>F</sub> =15A, di/dt=500A/μs	

Notes:

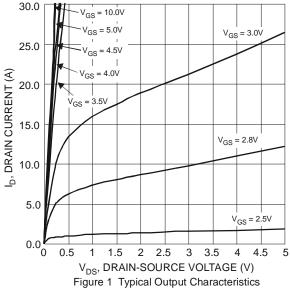
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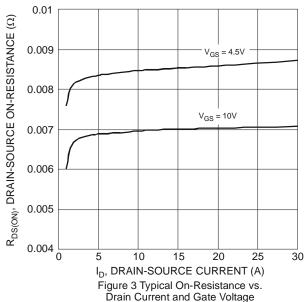
Device mounted on FR-4 substrate PC board, 2oz copper, with minimum recommended pad layout.
 Device mounted on FR-4 substrate PC board, 2oz copper, with thermal vias to bottom layer 1-inch square copper plate.

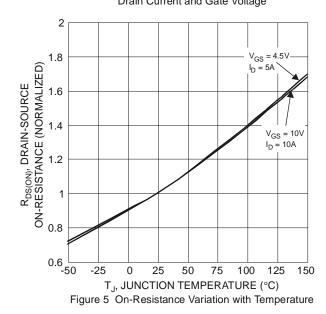
<sup>7.</sup> UIS in production with L = 1mH, TJ = +25°C.

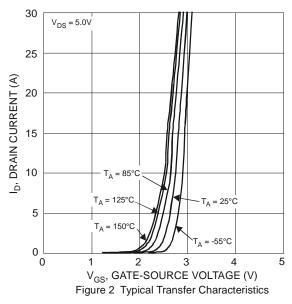
S. Short duration pulse test used to minimize self-heating effect.
 Guaranteed by design. Not subject to production testing.

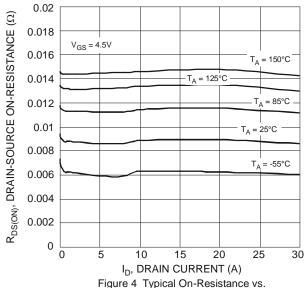












Drain Current and Temperature 0.02  $R_{DS(ON)}$ , DRAIN-SOURCE ON-RESISTANCE  $(\Omega)$ 0.018 0.016  $V_{GS} = 5.0V$ 0.014  $I_D = 5A$ 0.012 0.01 V<sub>GS</sub> = 10V 0.008 I<sub>D</sub> = 10A 0.006 0.004 0.002 25 50 75 100 125 -50 -25  $T_J$ , JUNCTION TEMPERATURE (°C)

Figure 6 On-Resistance Variation with Temperature



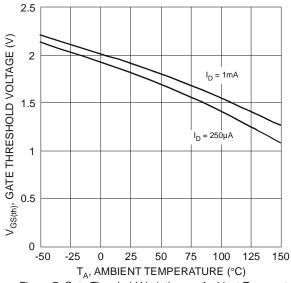
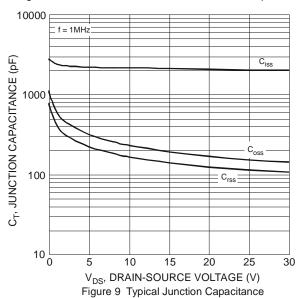
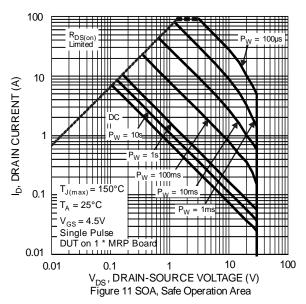
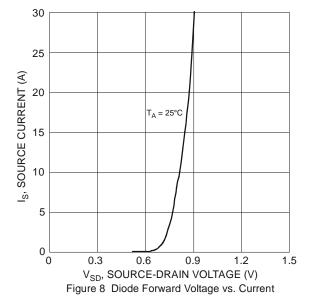
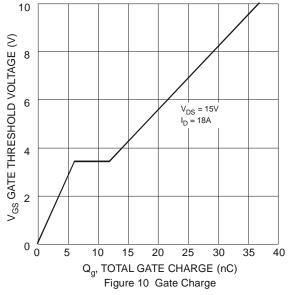


Figure 7 Gate Threshold Variation vs. Ambient Temperature

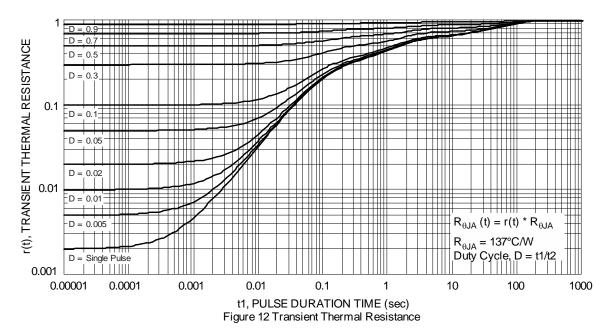








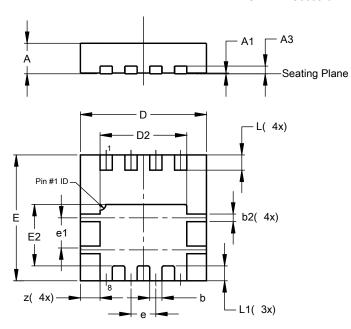




## **Package Outline Dimensions**

Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.

### POWERDI®3333-8



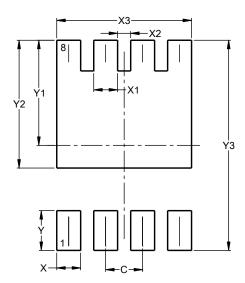
POWERDI®3333-8						
Dim	Min	Max	Тур			
Α	0.75	0.85	0.80			
A1	0.00	0.05	0.02			
<b>A</b> 3	1	-	0.203			
b	0.27	0.37	0.32			
b2	_	_	0.20			
D	3.25	3.35	3.30			
D2	2.22	2.32	2.27			
Е	3.25	3.35	3.30			
E2	1.56	1.66	1.61			
е	_	_	0.65			
e1	0.79	0.89	0.84			
۵	0.35	0.45	0.40			
L1	-	_	0.39			
Z	_	_	0.515			
All Dimensions in mm						



# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.

### POWERDI®3333-8



Dimensions	Value (in mm)
С	0.650
Х	0.420
X1	0.420
X2	0.230
Х3	2.370
Υ	0.700
Y1	1.850
Y2	2.250
Y3	3.700



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